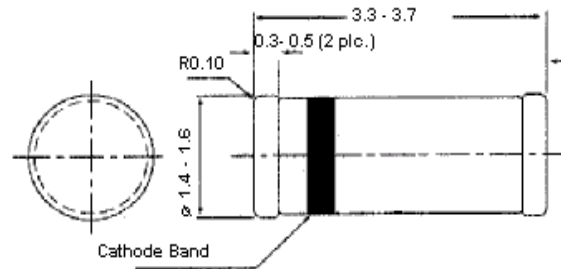


1N4148 mini-M.E.L.F. SIGNAL DIODE

Mechanical Data

Items	Material
Package	mini MELF
Case	Hermetically sealed glass
Lead/Finish	Double stud/Tin Plating
Chip	Glass Passivated



All dimensions are in mm

Mini MELF (LL-34), SOD - 80C
Hermetically Sealed, Glass Silicon Diodes

Absolute Maximum Ratings (Ta=25 °C)

	Symbol	Value	UNIT
Reverse Voltage	V_R	75	V
Reverse Recovery Time IF=-IR=10mA to IRR=-1mA VR=6V RL=100 ohms	trr	4	ns
Power Dissipation at Tamb= 25 °C 3.33mW/ °C	P_{tot}	500	mW
Forward Current	I_F	300	mA
Junction Temperature	T_j	-65 to +175	°C
Storage Temperature Range	T_s	-65 to +175	°C

Electrical Characteristics (Ta=25 °C)

	Symbol	Min	Max	Unit
Minimum Breakdown Voltage @IR= 100uA	BV	100	-	V
Rectifier Current (Average) Half Wave Rectification w/Resist Load at Ta= 25 °C and f > or = 50Hz	I_O	-	150	mA
Peak Forward Surge Current PW<1 sec	I_{Fsurge}	-	500	mA
Maximum Forward Voltage IF = 10 mA	V_F	-	1.0	V
Maximum reverse Leakage Current at $V_R = 20V$ at $V_R = 75V$ at $V_R = 20V, T_j = 150 °C$	I_R	-	0.025 5.0 50	uA
Maximum Junction Capacitance $V_F=V_R= 0, f= 1MHz$	C_j	-	4	pF
Reverse Recovery Time From IF=-IR=10mA to IRR=-1mA VR=6V RL=100 ohms	trr	-	4	ns
Maximum Thermal Resistance Junction to Ambient Air	R_{thJA}	-	0.35	°C/mW
Rectification Efficiency at f=100MHz, $V_{rf}= 2V$	nv	0.45	-	-